

L Number	Hits	Search Text	DB	Time stamp
1	1561906	low adj2 temperature and silicon adj3 carbide	USPAT	2003/10/17 10:24
2	6034	low adj2 temperature and silicon adj3 carbide	USPAT	2003/10/17 10:24
3	1	(low adj2 temperature and silicon adj3 carbide) and plasma adj2 etch?	USPAT	2003/10/17 10:25
4	1767	(low adj2 temperature and silicon adj3 carbide) and plasma	USPAT	2003/10/17 10:25
5	1113	((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen	USPAT	2003/10/17 10:25
6	834	((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen) and oxygen	USPAT	2003/10/17 10:25
7	0	((((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen) and oxygen) and etch?	USPAT	2003/10/17 10:25
8	228	((((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen) and oxygen) and semiconductor adj3 substrate	USPAT	2003/10/17 10:26
9	63	(((((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen) and oxygen) and semiconductor adj3 substrate) and etchant	USPAT	2003/10/17 10:36
10	0	etch? adj4 silicon adj2 carbide	USPAT	2003/10/17 10:36
11	146	etching adj4 silicon adj2 carbide	USPAT	2003/10/17 10:36
12	79	(etching adj4 silicon adj2 carbide) and plasma	USPAT	2003/10/17 10:37
13	28	((etching adj4 silicon adj2 carbide) and plasma) and low adj3 temperature	USPAT	2003/10/17 10:44
15	16	(((((etching adj4 silicon adj2 carbide) and plasma) and low adj3 temperature) and hydrogen) and oxygen	USPAT	2003/10/17 10:44
14	20	((((etching adj4 silicon adj2 carbide) and plasma) and low adj3 temperature) and hydrogen	USPAT	2003/10/17 10:45
-	177	cvd adj3 silicon adj3 carbide	USPAT	2003/10/17 10:23
-	0	(cvd adj3 silicon adj3 carbide) and plasma adj3 etch?	USPAT	2003/05/27 11:28
-	85	(cvd adj3 silicon adj3 carbide) and plasma	USPAT	2003/05/27 11:28
-	33	((cvd adj3 silicon adj3 carbide) and plasma) and hydrogen	USPAT	2003/05/27 11:28